

Plastic-Encapsulate Transistors

TRANSISTOR (PNP)

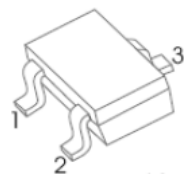
FEATURES

- Excellent h_{FE} linearity
- Complements the 2SC4081

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current	-150	mA
P_C	Collector Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	625	$^{\circ}\text{C/W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

SOT-323

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1. BASE
 2. EMITTER
 3. COLLECTOR

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu\text{A}, I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu\text{A}, I_C=0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB}=-60\text{V}, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-6\text{V}, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-6\text{V}, I_C=-1\text{mA}$	120		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-50\text{mA}, I_B=-5\text{mA}$			-0.5	V
Transition frequency	f_T	$V_{CE}=-12\text{V}, I_C=-2\text{mA}, f=30\text{MHz}$		140		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-12\text{V}, I_E=0, f=1\text{MHz}$		4	5	pF

CLASSIFICATION OF h_{FE}

Rank	Q	R	S
Range	120-270	180-390	270-560
Marking	FQ	FR	FS

Typical Characteristics

